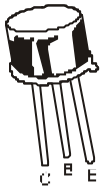
PNP SILICON PLANAR TRANSISTOR

2N3763

TO-39
Metal Can Package



ABSOLUTE MAXIMUM RATINGS

DESCRIPTION	SYMBOL	VALUE	UNIT
Collector Base Voltage	V_{CBO}	60	V
Collector Emitter Voltage	V_{CEO}	60	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	1.5	A
Power Dissipation at Ta=25ºC Derate Linearly at T_a > 25ºC	P_T	1.0	W
		5.71	mW/°C
Operating and Storage Junction Temperature Range	T_{op}, T_{stg}	- 55 to +200	ºC
Thermal Resistance Junction to Case	Rth (j-c)	60	ºC/W

ELECTRICAL CHARACTERISTICS (T_a=25ºC unless specified otherwise)

DESCRIPTION	SYMBOL	TEST CONDITION	MIN	MAX	UNIT
OFF CHARACTERISTICS					
Collector Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C= 10mA	60		V
Collector Base Cut Off Current	I_{CBO}	V_{CE} = 30V		100	nA
		V_{CE} = 60V		10	uA
Emitter Base Cut Off Current	I_{EBO}	V_{EB}=2V		200	nA
		V_{EB}=5V		10	uA
Collector Emitter Cut Off Current	I_{CEX}	V_{CE} = 30V, V_{EB} = 2.0V		100	nA
ON CHARACTERISTICS					
DC Gain	hFE	I_C=10mA, V_{CE}=1.0V	35		
		I_C=150mA, V_{CE}=1.0V	40		
		I_C=500mA, V_{CE}=1.0V	40	140	
		I_C=1.0A, V_{CE}=1.5V	20	80	
		I_C=1.5A, V_{CE}=5V	20		
Collector Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=10mA, I_B=1mA		0.1	V
		I_C=150mA, I_B=15mA		0.22	V
		I_C=500mA, I_B=50mA		0.5	V
		I_C=1.0A, I_B=100mA		0.9	V
Base Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=10mA, I_B=1mA		0.8	V
		I_C=150mA, I_B=15mA		1.0	V
		I_C=500mA, I_B=50mA		1.2	V
		I_C=1.0A, I_B=100mA	0.9	1.4	V

Pulse Test : Pulse width = 300us, Duty Cycle </= 2.0%

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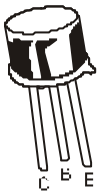

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DYNAMIC CHARACTERISTICS

DESCRIPTION	SYMBOL	TEST CONDITION	MIN	MAX	UNIT
Output Capacitance	C_{obo}	V_{CB}=10V, I_E=0, 100KHz < f < 1.0MHz		25	pF
Input Capacitance	C_{ibo}	V_{BE}=0.5V, I_C=0, 100KHz < f < 1.0MHz		80	pF

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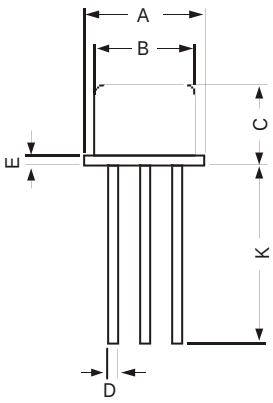
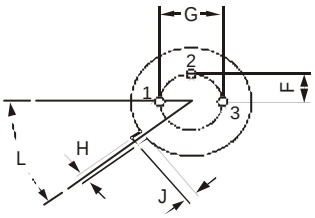
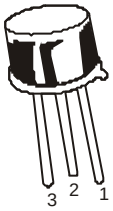
TO-39 Metal Can Package



All dimensions are in mm

DIM	MIN	MAX
A	8.50	9.39
B	7.74	8.50
C	6.09	6.60
D	0.40	0.53
E	—	0.88
F	2.41	2.66
G	4.82	5.33
H	0.71	0.86
J	0.73	1.02
K	12.70	—
L	42 DEG	48 DEG





PIN CONFIGURATION
1. EMITTER
2. BASE
3. COLLECTOR

Packing Detail

PACKAGE	STANDARD PACK		INNER CARTON BOX		OUTER CARTON BOX		
	Details	Net Weight/Qty	Size	Qty	Size	Qty	Gr Wt
TO-39	500 pcs/polybag	540 gm/500 pcs	3" x 7.5" x 7.5"	20K	17" x 15" x 13.5"	32K	40 kgs

Component Disposal Instructions

1. CDIL Semiconductor Devices are RoHS compliant, customers are requested to please dispose as per prevailing Environmental Legislation of their Country.
2. In Europe, please dispose as per EU Directive 2002/96/EC on Waste Electrical and Electronic Equipment (WEEE).

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Customer Notes

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Disclaimer

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